

This IC includes high-accuracy voltage detection circuits and delay circuits, and can monitor the status of 3-serial to 5-serial cell lithium-ion rechargeable batteries through small 8-pin packages.

Short-circuiting between cells makes it possible for serial connection of 3-cell to 5-cell.

■ Features

- High-accuracy voltage detection circuit for each cell

| | | |
|---|----------------------------------|---|
| Overcharge detection voltage n | 3.500 V to 4.700 V (5 mV step) | Accuracy ± 15 mV ($T_a = +25^\circ\text{C}$) |
| | | Accuracy ± 20 mV ($T_a = -10^\circ\text{C}$ to $+60^\circ\text{C}$) |
| Overcharge release voltage n ^{*1} | 3.100 V to 4.700 V | Accuracy ± 50 mV |
| Overdischarge detection voltage n | 1.500 V to 3.200 V (50 mV step) | Accuracy ± 80 mV |
| Overdischarge release voltage n ^{*2} | 1.500 V to 3.900 V (100 mV step) | Accuracy ± 100 mV |
- Delay times are generated only by an internal circuit (external capacitors are unnecessary)

| | |
|-------------------------------------|--------------------------------|
| Overcharge detection delay time: | 0.5 s, 1 s, 2 s, 4 s, 6 s, 8 s |
| Overdischarge detection delay time: | 128 ms, 256 ms, 0.5 s, 1 s |
- CO and DO pin output voltage is limited to 7.5 V max. respectively
- CO pin, DO pin output form: CMOS output, Nch open-drain output
- CO pin, DO pin output logic: Active "H", active "L"
- High-withstand voltage: Absolute maximum rating 28 V
- Wide operation voltage range: 3.6 V to 24 V
- Wide operation temperature range: $T_a = -40^\circ\text{C}$ to $+85^\circ\text{C}$
- Low current consumption

| | |
|---|------------------------|
| During operation (3.4 V for each cell): | 7.0 μA max. |
|---|------------------------|
- Lead-free (Sn 100%), halogen-free

*1. Overcharge release voltage = Overcharge detection voltage – Overcharge hysteresis voltage
(Overcharge hysteresis voltage can be selected from a range of 0 mV to 400 mV in 50 mV step.)

*2. Overdischarge release voltage = Overdischarge detection voltage + Overdischarge hysteresis voltage
(Overdischarge hysteresis voltage can be selected from a range of 0 mV to 700 mV in 100 mV step.)

Remark n = 1, 2, 3, 4, 5

■ Applications

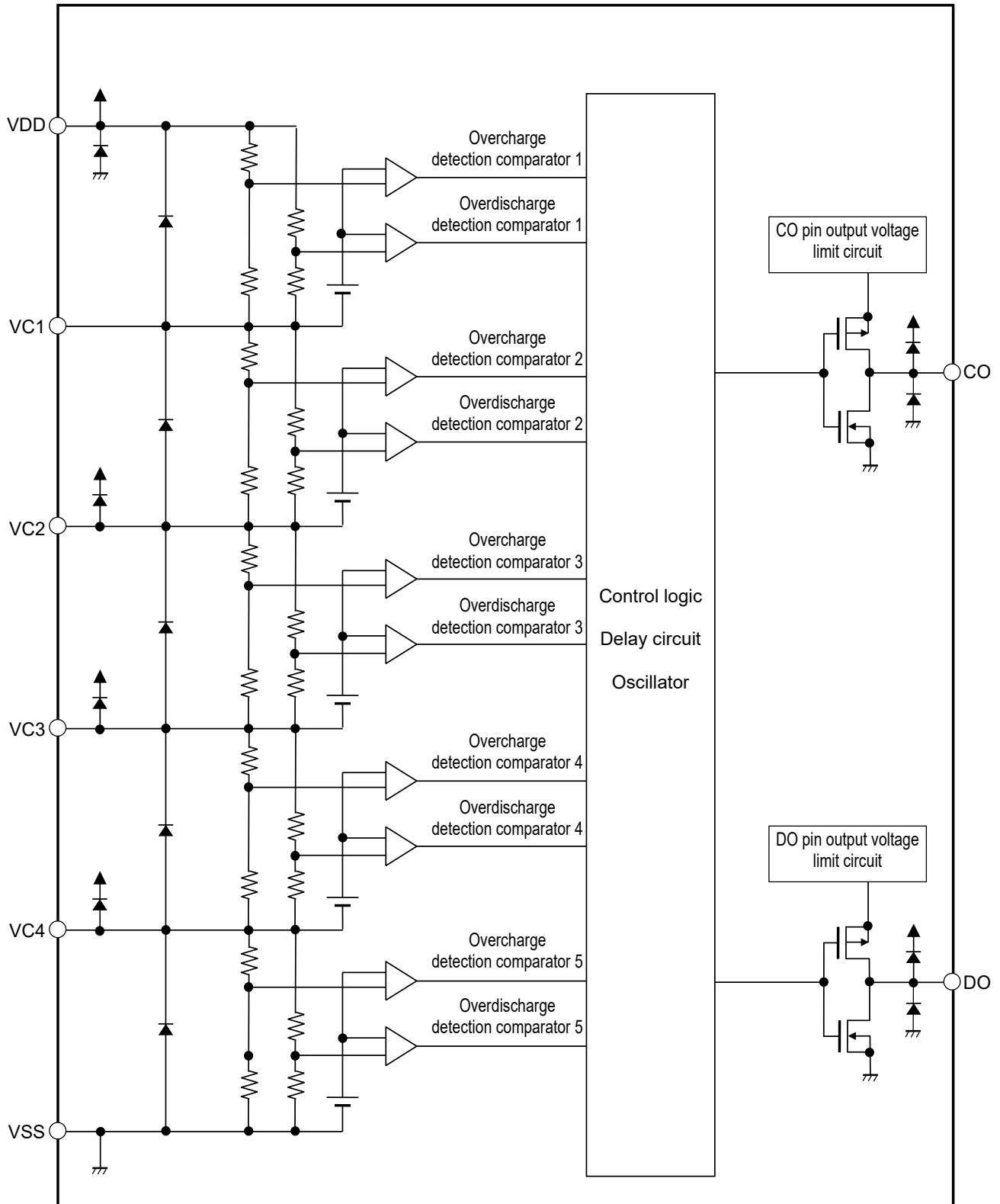
- Lithium-ion rechargeable battery pack

■ Packages

- TMSOP-8
- SNT-8A

■ **Block Diagram**

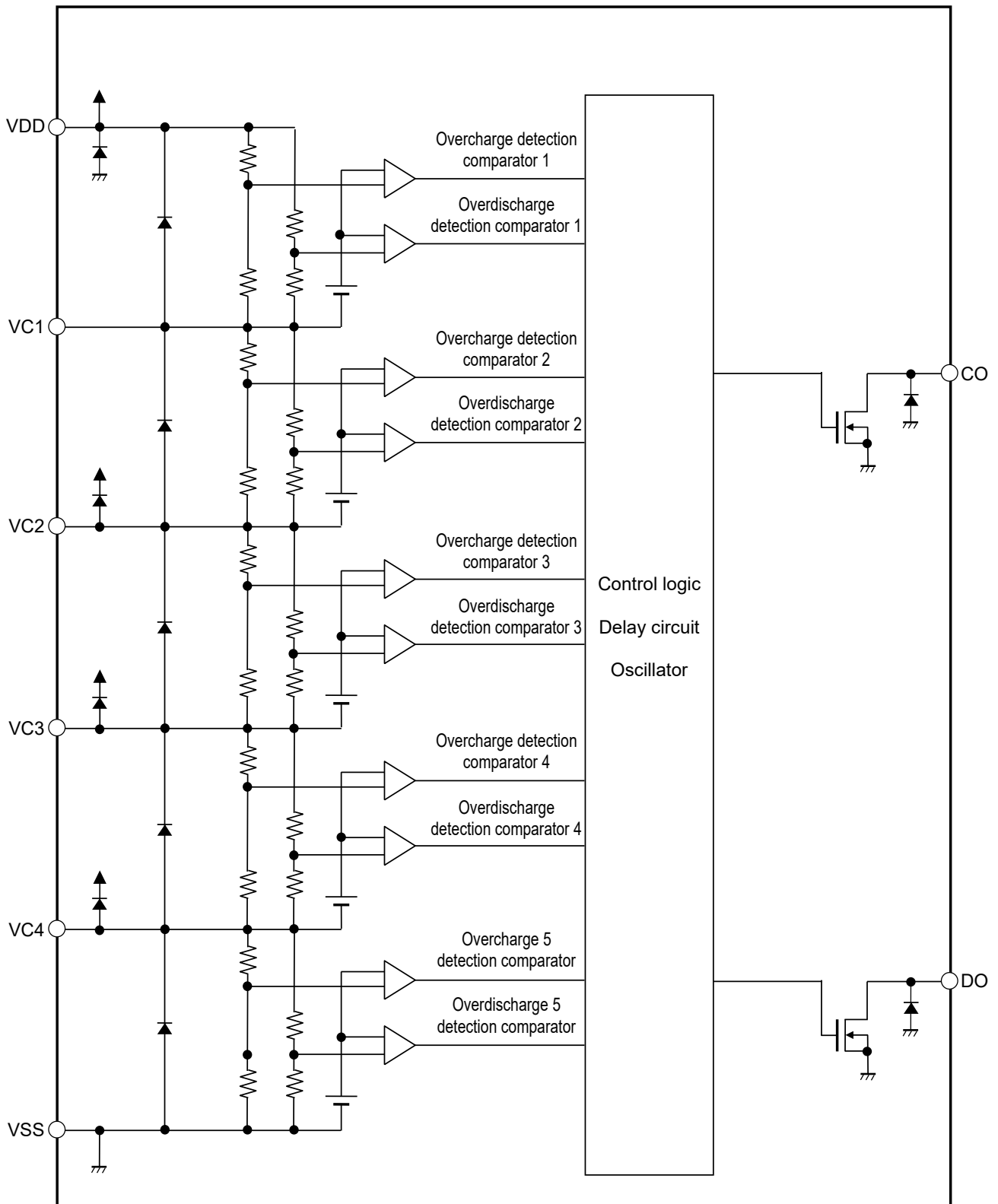
1. CMOS output product



Remark Diodes in the figure are parasitic diodes.

Figure 1

2. Nch open-drain output product

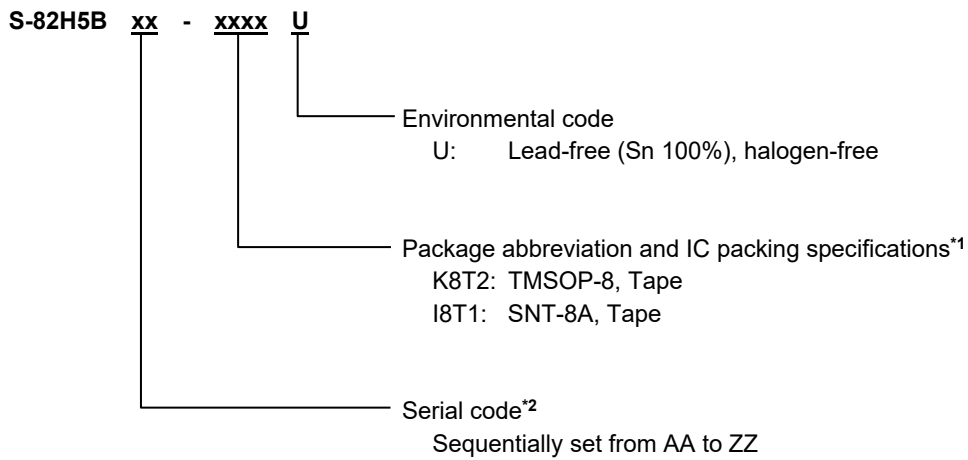


Remark Diodes in the figure are parasitic diodes.

Figure 2

■ **Product Name Structure**

1. **Product name**



*1. Refer to the tape drawing.

*2. Refer to "3. Product name list".

2. **Package**

Table 1 Package Drawing Codes

| Package Name | Dimension | Tape | Reel | Land |
|--------------|--------------|--------------|--------------|--------------|
| TMSOP-8 | FM008-A-P-SD | FM008-A-C-SD | FM008-A-R-SD | - |
| SNT-8A | PH008-A-P-SD | PH008-A-C-SD | PH008-A-R-SD | PH008-A-L-SD |

BATTERY MONITORING IC FOR 3-SERIAL TO 5-SERIAL CELL PACK

Rev.1.0_00

S-82H5B Series

3. Product name list

3.1 TMSOP-8

Table 2 (1 / 2)

| Product Name | Overcharge Detection Voltage [V _{CU}] | Overcharge Release Voltage [V _{CL}] | Overdischarge Detection Voltage [V _{DL}] | Overdischarge Release Voltage [V _{DU}] | Overcharge Detection Delay Time* ¹ [t _{CU}] | Overdischarge Detection Delay Time* ² [t _{DL}] |
|-----------------|--|--|---|---|---|--|
| S-82H5BAA-K8T2U | 4.275 V | 4.225 V | 2.000 V | 2.200 V | 1.0 s | 1.0 s |

Table 2 (2 / 2)

| Product Name | CO Pin Output Form | CO Pin Output Logic | DO Pin Output Form | DO Pin Output Logic |
|-----------------|-----------------------|---------------------|--------------------|---------------------|
| S-82H5BAA-K8T2U | Nch open-drain output | Active "L" | CMOS output | Active "H" |

*1. Overcharge detection delay time: 0.5 s, 1 s, 2 s, 4 s, 6 s, 8 s

*2. Overdischarge detection delay time: 128 ms, 256 ms, 0.5 s, 1 s

Remark Please contact our sales representatives for products other than the above.

■ **Pin Configuration**

1. TMSOP-8

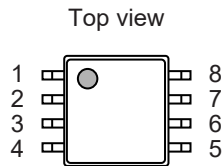


Figure 3

Table 3

| Pin No. | Symbol | Description |
|---------|--------|---|
| 1 | VDD | Positive power supply input pin, Positive voltage connection pin of battery 1 |
| 2 | VC1 | Negative voltage connection pin of battery 1, Positive voltage connection pin of battery 2 |
| 3 | VC2 | Negative voltage connection pin of battery 2, Positive voltage connection pin of battery 3 |
| 4 | VC3 | Negative voltage connection pin of battery 3, Positive voltage connection pin of battery 4 |
| 5 | VC4 | Negative voltage connection pin of battery 4, Positive voltage connection pin of battery 5 |
| 6 | VSS | Negative power supply input pin, Negative voltage connection pin of battery 5 |
| 7 | DO | Overdischarge detection output pin |
| 8 | CO | Overcharge detection output pin |

2. SNT-8A

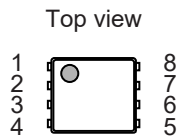


Figure 4

Table 4

| Pin No. | Symbol | Description |
|---------|--------|---|
| 1 | VDD | Positive power supply input pin, Positive voltage connection pin of battery 1 |
| 2 | VC1 | Negative voltage connection pin of battery 1, Positive voltage connection pin of battery 2 |
| 3 | VC2 | Negative voltage connection pin of battery 2, Positive voltage connection pin of battery 3 |
| 4 | VC3 | Negative voltage connection pin of battery 3, Positive voltage connection pin of battery 4 |
| 5 | VC4 | Negative voltage connection pin of battery 4, Positive voltage connection pin of battery 5 |
| 6 | VSS | Negative power supply input pin, Negative voltage connection pin of battery 5 |
| 7 | DO | Overdischarge detection output pin |
| 8 | CO | Overcharge detection output pin |

BATTERY MONITORING IC FOR 3-SERIAL TO 5-SERIAL CELL PACK
S-82H5B Series

Rev.1.0_00

■ **Absolute Maximum Ratings**

Table 5

(Ta = +25°C unless otherwise specified)

| Item | | Symbol | Applied Pin | Absolute Maximum Rating | Unit |
|---|-------------------------------|------------------|-------------|--|------|
| Input voltage between VDD pin and VSS pin | | V _{DS} | VDD | V _{SS} - 0.3 to V _{SS} + 28 | V |
| Input pin voltage | | V _{IN1} | VC1 | V _{DD} - 6.0 to V _{DD} + 0.3, V _{IN2} - 0.3 to V _{IN2} + 6.0 | V |
| | | V _{IN2} | VC2 | V _{IN3} - 0.3 to V _{IN3} + 6.0, V _{IN3} - 0.3 to V _{DD} + 0.3 | V |
| | | V _{IN3} | VC3 | V _{IN4} - 0.3 to V _{IN4} + 6.0, V _{IN4} - 0.3 to V _{DD} + 0.3 | V |
| | | V _{IN4} | VC4 | V _{SS} - 0.3 to V _{SS} + 6.0, V _{SS} - 0.3 to V _{DD} + 0.3 | V |
| Output pin voltage | CMOS output product | V _{OUT} | DO | V _{SS} - 0.3 to V _{DD} + 0.3 | V |
| | | | CO | V _{SS} - 0.3 to V _{DD} + 0.3 | V |
| | Nch open-drain output product | | DO | V _{SS} - 0.3 to V _{SS} + 28 | V |
| | | | CO | V _{SS} - 0.3 to V _{SS} + 28 | V |
| Operation ambient temperature | | T _{opr} | - | -40 to +85 | °C |
| Storage temperature | | T _{stg} | - | -40 to +125 | °C |

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ **Thermal Resistance Value**

Table 6

| Items | Symbol | Condition | Min. | Typ. | Max. | Unit | |
|--|-----------------|-----------|---------|------|------|------|------|
| Junction-to-ambient thermal resistance*1 | θ _{JA} | TMSOP-8 | Board A | - | 160 | - | °C/W |
| | | | Board B | - | 133 | - | °C/W |
| | | | Board C | - | - | - | °C/W |
| | | | Board D | - | - | - | °C/W |
| | | | Board E | - | - | - | °C/W |
| | | SNT-8A | Board A | - | 211 | - | °C/W |
| | | | Board B | - | 173 | - | °C/W |
| | | | Board C | - | - | - | °C/W |
| | | | Board D | - | - | - | °C/W |
| | | | Board E | - | - | - | °C/W |

*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ Power Dissipation" and "Test Board" for details.

■ **Electrical Characteristics**

Table 7

(Ta = +25°C unless otherwise specified)

| Item | Symbol | Condition | Min. | Typ. | Max. | Unit | Test Circuit |
|--|-----------------------------|--|-------------------------|-----------------|-------------------------|------|--------------|
| Detection Voltage | | | | | | | |
| Overcharge detection voltage n (n = 1, 2, 3, 4, 5) | V _{CU_n} | V1 = V2 = V3 = V4 = V5 = V _{CU} - 0.1 V | V _{CU} - 0.015 | V _{CU} | V _{CU} + 0.015 | V | 1 |
| | | Ta = -10°C to +60°C*1, V1 = V2 = V3 = V4 = V5 = V _{CU} - 0.1 V | V _{CU} - 0.020 | V _{CU} | V _{CU} + 0.020 | V | 1 |
| Overcharge release voltage n (n = 1, 2, 3, 4, 5) | V _{CL_n} | - | V _{CL} - 0.050 | V _{CL} | V _{CL} + 0.050 | V | 2 |
| Overdischarge detection voltage n (n = 1, 2, 3, 4, 5) | V _{DL_n} | - | V _{DL} - 0.08 | V _{DL} | V _{DL} + 0.08 | V | 2 |
| Overdischarge release voltage n (n = 1, 2, 3, 4, 5) | V _{DU_n} | - | V _{DU} - 0.10 | V _{DU} | V _{DU} + 0.10 | V | 2 |
| Input Voltage | | | | | | | |
| Operation voltage between VDD pin and VSS pin | V _{DSOP} | - | 3.6 | - | 24 | V | - |
| Output Voltage | | | | | | | |
| CO pin voltage "H" | V _{COH} | CMOS output product | 5.0 | 6.0 | 7.5 | V | 2 |
| DO pin voltage "H" | V _{DOH} | CMOS output product | 5.0 | 6.0 | 7.5 | V | 2 |
| Input Current | | | | | | | |
| Current consumption during operation | I _{oPE} | V1 = V2 = V3 = V4 = V5 = 3.4 V | - | 2.5 | 7.0 | μA | 2 |
| V _{Cn} pin current (n = 1, 2, 3, 4) | I _{V_{Cn}} | V1 = V2 = V3 = V4 = V5 = 3.4 V | -1.0 | 0 | 1.0 | μA | 2 |
| Output Current | | | | | | | |
| DO pin sink current | I _{DOL} | - | 20 | - | - | μA | 2 |
| DO pin source current | I _{DOH} | CMOS output product | - | - | -20 | μA | 2 |
| DO pin leakage current | I _{DOLL} | Nch open-drain output product | - | - | 0.1 | μA | 2 |
| CO pin sink current | I _{COL} | - | 20 | - | - | μA | 2 |
| CO pin source current | I _{COH} | CMOS output product | - | - | -20 | μA | 2 |
| CO pin leakage current | I _{COLL} | Nch open-drain output product | - | - | 0.1 | μA | 2 |
| Delay Time | | | | | | | |
| Overcharge detection delay time | t _{CU} | - | t _{CU} × 0.7 | t _{CU} | t _{CU} × 1.3 | - | 2 |
| Overdischarge detection delay time | t _{DL} | - | t _{DL} × 0.7 | t _{DL} | t _{DL} × 1.3 | - | 2 |

*1. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.

■ **Test Circuits**

Set the initial status of the test circuit as follows.

Table 8

| Test Items | CO Pin Output Form | DO Pin Output Form | SW1 | SW2 | SW3 | SW4 | SW5 | SW6 |
|--|-----------------------|-----------------------|-----|-----|-----|-----|-----|-----|
| Current consumption during operation, CO pin sink current, CO pin leakage current, DO pin sink current, DO pin leakage current | - | - | OFF | OFF | OFF | OFF | OFF | OFF |
| Other than the above | CMOS output | CMOS output | OFF | OFF | OFF | OFF | OFF | OFF |
| | CMOS output | Nch open-drain output | ON | OFF | OFF | OFF | OFF | OFF |
| | Nch open-drain output | CMOS output | OFF | ON | OFF | OFF | OFF | OFF |
| | Nch open-drain output | Nch open-drain output | ON | ON | OFF | OFF | OFF | OFF |

1. Overcharge detection voltage n (V_{CU_n})
(Test circuit 1)

After setting $V1 = V2 = V3 = V4 = V5 = V_{CU} - 0.1 V$, $V1$ is gradually increased. When the CO pin output inverts, the voltage $V1$ is defined as the overcharge detection voltage 1 (V_{CU1}). Other overcharge detection voltage n (V_{CU_n}) can be determined in the same way as when $n = 1$.

2. Overcharge release voltage n (V_{CL_n})
(Test circuit 2)

Set $V1 = V_{CU} + 0.1 V$, $V2 = V3 = V4 = V5 = V_{CL} - 0.1 V$ and invert the CO pin output. After that, $V1$ is gradually decreased. When the CO pin output inverts again, the voltage $V1$ is defined as the overcharge release voltage (V_{CL1}). Other overcharge release voltage n (V_{CL_n}) can be determined in the same way as when $n = 1$.

3. Overdischarge detection voltage n (V_{DL_n}), overdischarge release voltage n (V_{DU_n})
(Test circuit 2)

After setting $V1 = V2 = V3 = V4 = V5 = V_{DL} + 0.1 V$, $V1$ is gradually decreased. When the DO pin output inverts, the voltage $V1$ is defined as the overdischarge detection voltage 1 (V_{DL1}). After that, set $V2 = V3 = V4 = V5 = V_{DU} + 0.15 V$. $V1$ is gradually increased. When the DO pin output inverts again, the voltage $V1$ is defined as overdischarge release voltage 1 (V_{DU1}). Other overdischarge detection voltage n (V_{DL_n}) and overdischarge release voltage n (V_{DU_n}) can be determined in the same way as when $n = 1$.

Remark n = 1, 2, 3, 4, 5

**4. CO pin output voltage "H" (V_{COH}), DO pin output voltage "H" (V_{DOH})
(Test circuit 2)**

4.1 CO pin output logic active "H"

The CO pin output voltage "H" (V_{COH}) is the voltage between the CO pin and the VSS pin when setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $I2 = 0.1\text{ }\mu\text{A}$ and SW6 ON.

4.2 CO pin output logic active "L"

The CO pin output voltage "H" (V_{COH}) is the voltage between the CO pin and the VSS pin when setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $I2 = 0.1\text{ }\mu\text{A}$ and SW6 ON.

4.3 DO pin output logic active "H"

The DO pin output voltage "H" (V_{DOH}) is the voltage between the DO pin and the VSS pin when setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $I1 = 0.1\text{ }\mu\text{A}$ and SW5 ON.

4.4 DO pin output logic active "L"

The DO pin output voltage "H" (V_{DOH}) is defined as the voltage between the DO pin and the VSS pin when setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $I1 = 0.1\text{ }\mu\text{A}$ and SW5 ON.

**5. CO pin source current (I_{COH}), CO pin sink current (I_{COL}), CO pin leakage current (I_{COLL}),
DO pin source current (I_{DOH}), DO pin sink current (I_{DOL}), DO pin leakage current (I_{DOLL})
(Test circuit 2)**

5.1 CO pin CMOS output product

5.1.1 CO pin output logic active "H"

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = V_{COH} - 0.5\text{ V}$. The CO pin current is the CO pin source current (I_{COH}) at that time.

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.1.2 CO pin output logic active "L"

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = V_{COH} - 0.5\text{ V}$. The CO pin current is the CO pin source current (I_{COH}) at that time.

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.2 CO pin Nch open-drain output Product

5.2.1 CO pin output logic active "H"

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = 17\text{ V}$. The CO pin current is the CO pin leakage current (I_{COLL}) at this time.

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.2.2 CO pin output logic active "L"

Set SW4 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V7 = 17\text{ V}$. The CO pin current is the CO pin leakage current (I_{COLL}) at this time.

Set SW4 to ON after setting $V1 = 4.8\text{ V}$, $V2 = V3 = V4 = V5 = 3.05\text{ V}$, $V7 = 0.5\text{ V}$. The CO pin current is the CO pin sink current (I_{COL}) at that time.

5.3 DO pin CMOS output product

5.3.1 DO pin output logic active "H"

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = V_{\text{DOH}} - 0.5\text{ V}$. The DO pin current is the DO pin source current (I_{DOH}) at this time.

Set SW3 to ON after setting $V1 = 4.8\text{ V}$, $V2 = 4.1\text{ V}$, $V3 = 4.1\text{ V}$, $V4 = 4.0\text{ V}$, $V5 = 0\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

5.3.2 DO pin output logic active "L"

Set SW3 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V6 = V_{\text{DOH}} - 0.5\text{ V}$. The DO pin current is the DO pin source current (I_{DOH}) at this time.

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

5.4 DO pin Nch open-drain output product

5.4.1 DO pin output logic active "H"

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = 17\text{ V}$. The DO pin current is the DO pin leak current (I_{DOLL}) at this time.

Set SW3 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

5.4.2 DO pin output logic active "L"

Set SW3 to ON after setting $V1 = V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V6 = 17\text{ V}$. The DO pin current is the DO pin leak current (I_{DOLL}) at this time.

Set SW3 to ON after setting $V1 = 1.4\text{ V}$, $V2 = V3 = V4 = V5 = 3.9\text{ V}$, $V6 = 0.5\text{ V}$. The DO pin current is the DO pin sink current (I_{DOL}) at this time.

6. Overcharge detection delay time (t_{CU}) (Test circuit 2)

After setting $V5 = V_{\text{CU}} - 0.2\text{ V}$, $V1 = V2 = V3 = V4 = 3.4\text{ V}$, $V5$ is increased to $V_{\text{CU}} + 0.2\text{ V}$. The overcharge detection delay time (t_{CU}) is the time period until the CO pin output inverts.

7. Overdischarge detection delay time (t_{DL}) (Test circuit 2)

After setting $V5 = V_{\text{DL}} + 0.2\text{ V}$, $V2 = V3 = V4 = V5 = 3.4\text{ V}$, $V5$ is decreased to $V_{\text{DL}} - 0.2\text{ V}$. The overdischarge detection delay time (t_{DL}) is the time period until the DO pin output inverts.

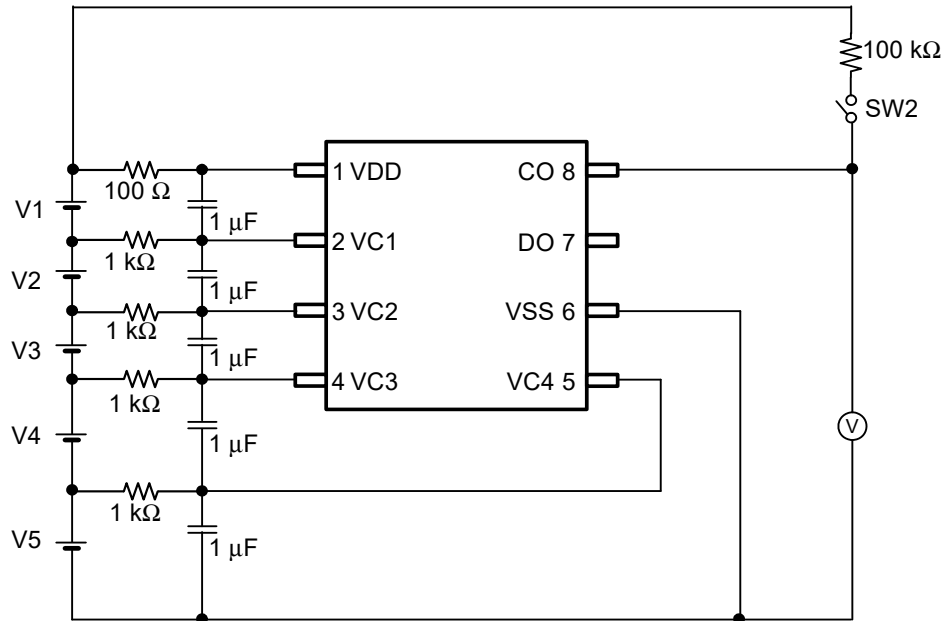


Figure 5 Test Circuit 1

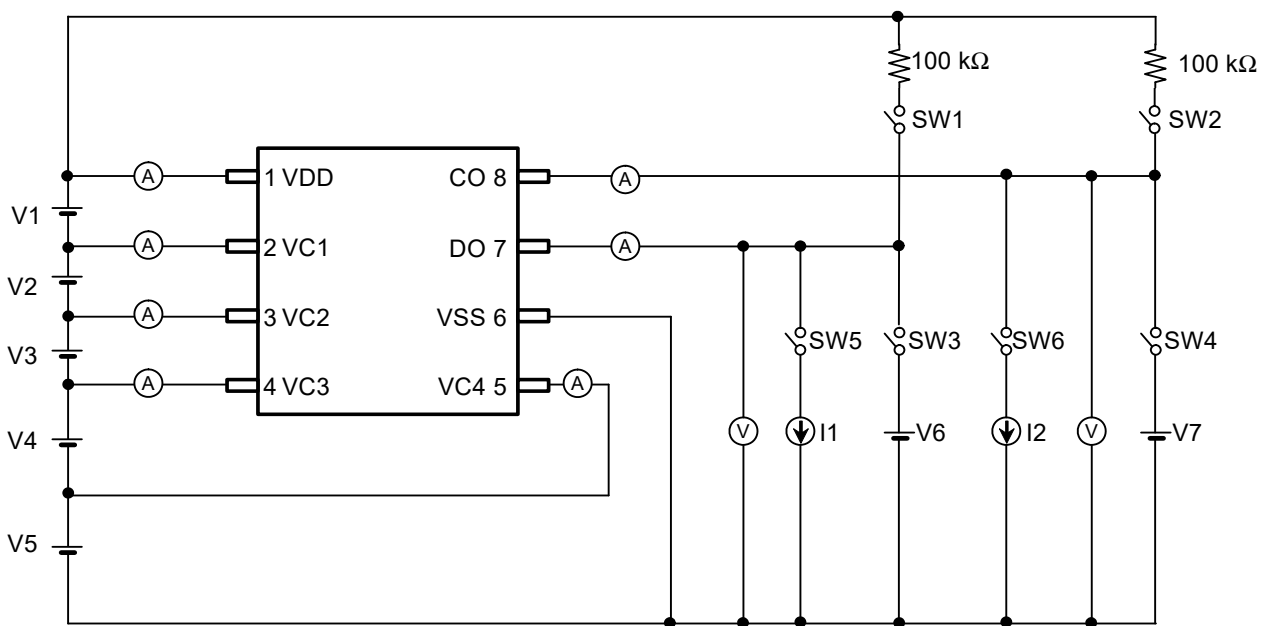


Figure 6 Test Circuit 2

■ **Operation**

1. Normal status

When the voltage of all batteries is in the range between the overdischarge detection voltage n (V_{DLn}) and the overcharge detection voltage (V_{CUn}), the CO pin output is shown in **Table 9**, and the DO pin output is shown in **Table 10**. This status is called the normal status.

Table 9

| CO Pin Output Logic | CO Pin Output |
|---------------------|---------------|
| Active "H" | "L" |
| Active "L" | "H" |

Table 10

| DO Pin Output Logic | DO Pin Output |
|---------------------|---------------|
| Active "H" | "L" |
| Active "L" | "H" |

2. Overcharge status

When the voltage of any of the batteries exceeds the overcharge detection voltage n (V_{CUn}) during charging and this condition continues for the overcharge detection delay time (t_{CU}) or longer, the CO pin output inverts. This status is called the overcharge status.

When the voltage of all batteries falls below the overcharge release voltage n (V_{CLn}), the overcharge status is released, and this IC returns to its normal status.

3. Overdischarge status

When the voltage of any of the batteries falls below the overdischarge detection voltage n (V_{DLn}) during discharging and the status continues for the overdischarge detection delay time (t_{DL}) or longer, the DO pin output inverts. This status is called the overdischarge status.

When the voltage of all batteries becomes overdischarge release voltage n (V_{DU_n}) or higher, this IC returns to normal status.

4. Test mode

In this IC, the overcharge detection delay time (t_{CU}) and the overdischarge delay time (t_{DL}) can be shortened by entering the test mode.

This IC transitions to the test mode by setting the DO pin voltage to the following voltage while the IC is in the normal status.

Table 11

| DO Pin Output Form | DO Pin Output Logic | DO Pin Voltage |
|-----------------------|---------------------|----------------|
| CMOS output | Active "L" | 0 V |
| CMOS output | Active "H" | 5 V |
| Nch open-drain output | – | $V_{DD} + 5 V$ |

In the test mode, overdischarge status output is output from the CO pin, not the DO pin.

After transitioning to the test mode, the test mode is retained even if this IC transitions to the overcharge status or the overdischarge status by retaining the DO pin voltage.

The test mode is released when the DO pin voltage input is returned to normal status output.

Caution Set the test mode when all batteries are neither overcharged nor overdischarged.

Remark $n = 1, 2, 3, 4, 5$

■ **Timing Charts**

1. **Overcharge detection operation**

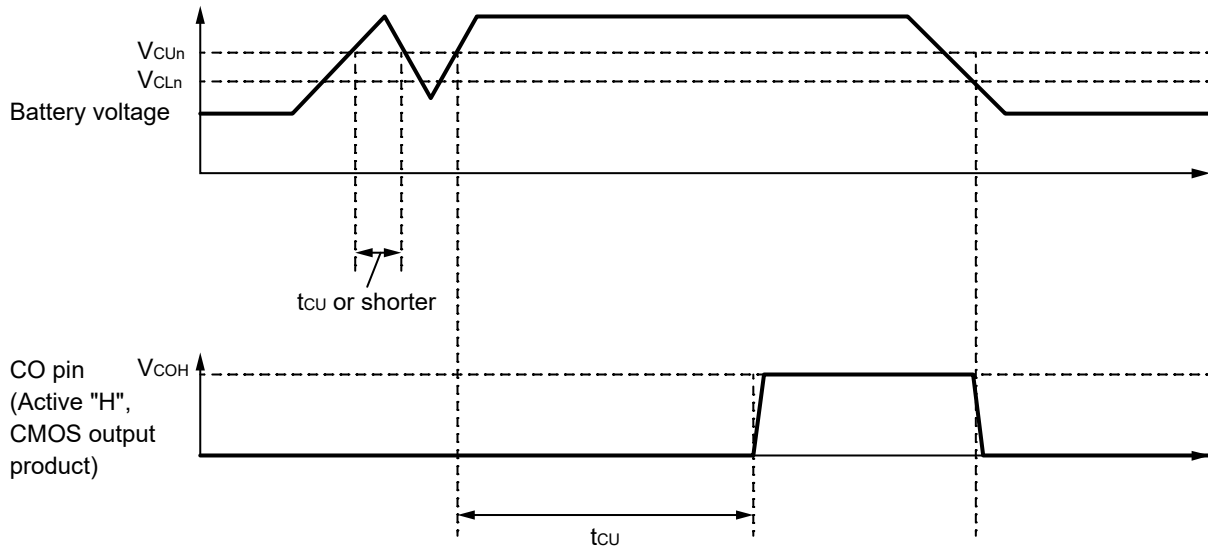


Figure 7

2. **Overdischarge detection operation**

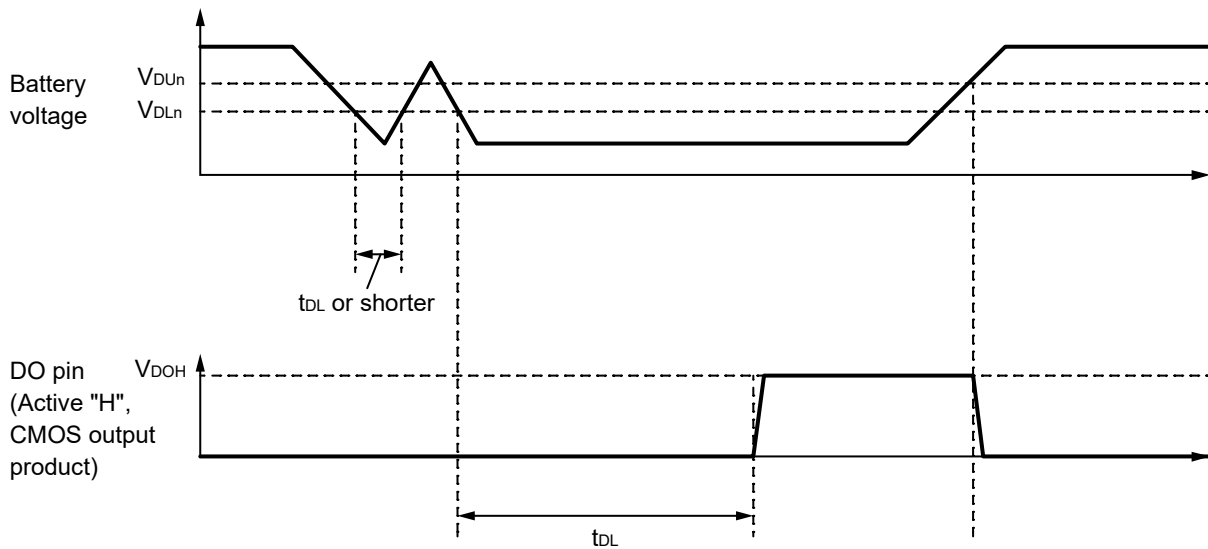


Figure 8

Remark n = 1, 2, 3, 4, 5

■ **Connection Examples of Battery Monitoring IC**

1. 5-serial cell (CO pin output form: CMOS output, DO pin output form: CMOS output)

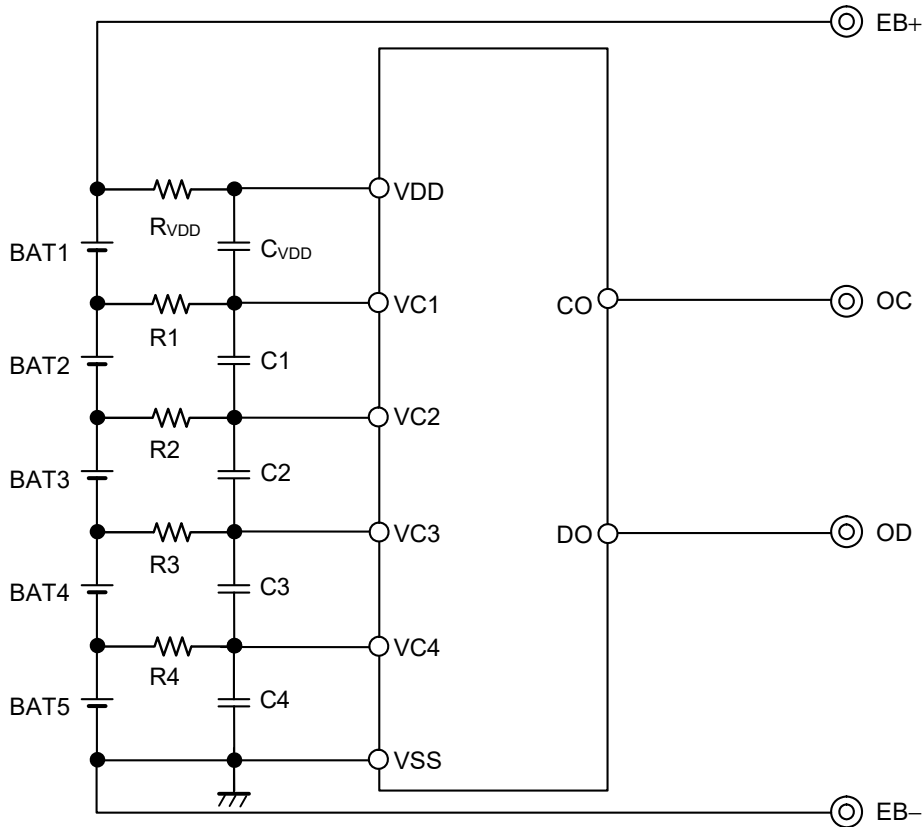


Figure 9

Table 12 Constants for External Components

| No. | Part | Typ. | Unit |
|-----|----------------|------|------|
| 1 | R1 to R4 | 1 | kΩ |
| 2 | C1 to C4, CvDD | 1 | μF |
| 3 | RvDD | 100 | Ω |

- Caution**
1. The constants may be changed without notice.
 2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

2. 4-serial cell (CO pin output form: CMOS output, DO pin output form: CMOS output)

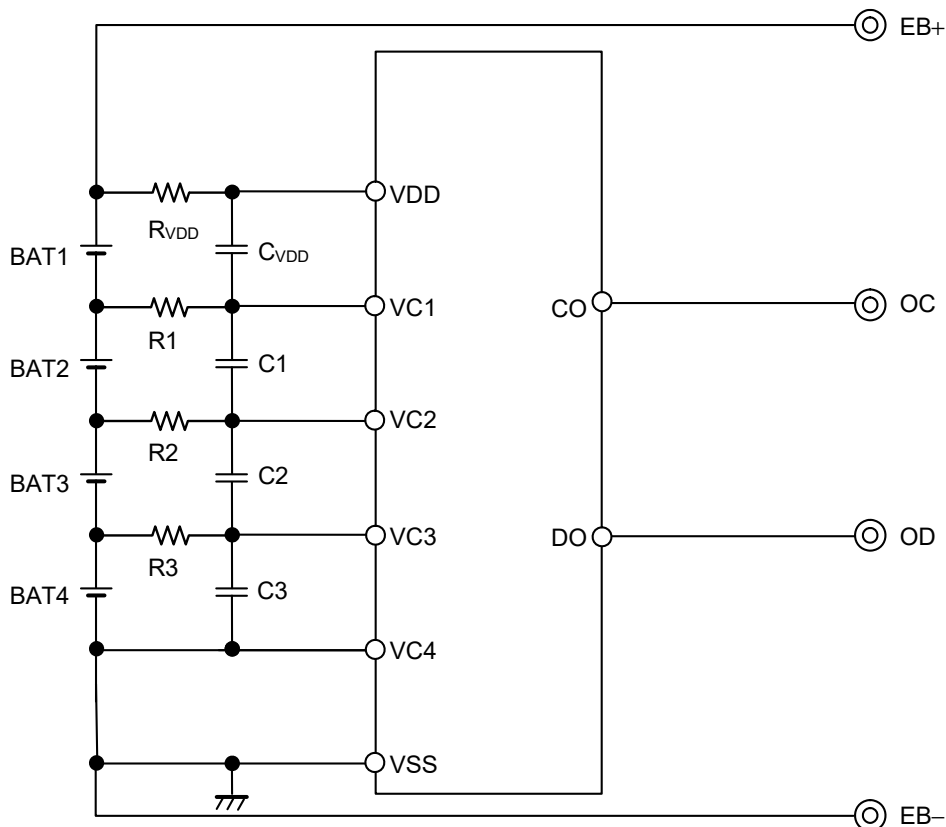


Figure 10

Table 13 Constants for External Components

| No. | Part | Typ. | Unit |
|-----|----------------|------|------|
| 1 | R1 to R3 | 1 | kΩ |
| 2 | C1 to C3, CVDD | 1 | μF |
| 3 | RVDD | 100 | Ω |

- Caution**
1. The constants may be changed without notice.
 2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

3. 3-serial cell (CO pin output form: CMOS output, DO pin output form: CMOS output)

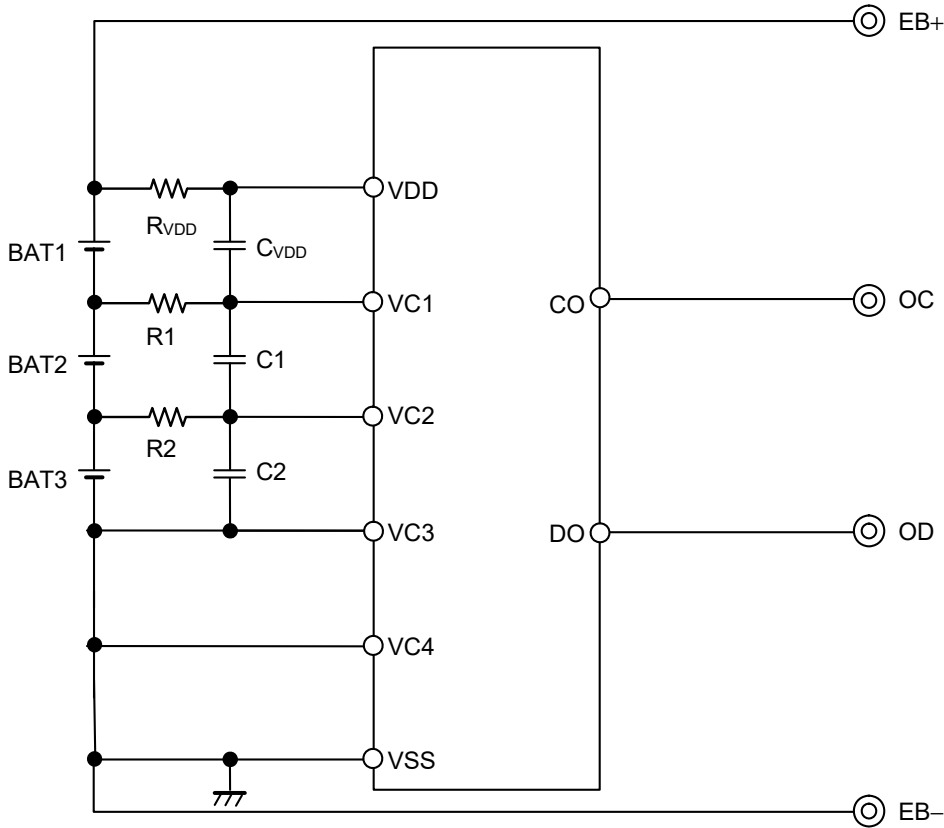


Figure 11

Table 14 Constants for External Components

| No. | Part | Typ. | Unit |
|-----|--------------|------|------|
| 1 | R1, R2 | 1 | kΩ |
| 2 | C1, C2, CvDD | 1 | μF |
| 3 | RvDD | 100 | Ω |

- Caution**
1. The constants may be changed without notice.
 2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

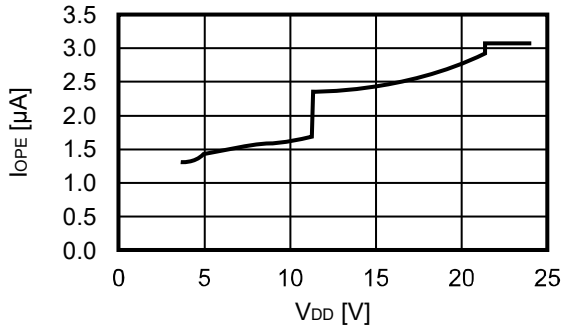
■ **Precautions**

- The application conditions for the input voltage, output voltage, and load current should not exceed the power dissipation.
- If an overcharged battery and an overdischarged battery intermix, this IC will change to the overcharge and overdischarge statuses.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

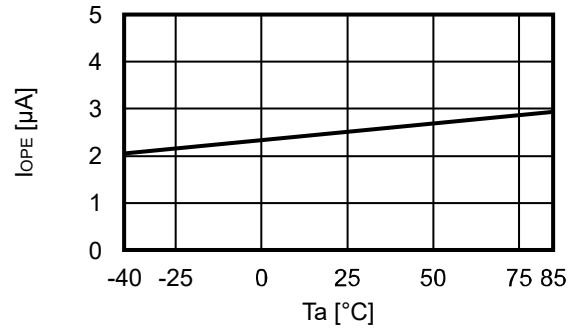
■ Characteristics (Typical Data)

1. Current consumption

1.1 I_{OPE} vs. V_{DD}

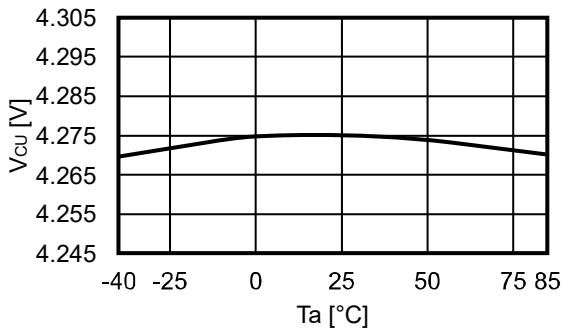


1.2 I_{OPE} vs. T_a

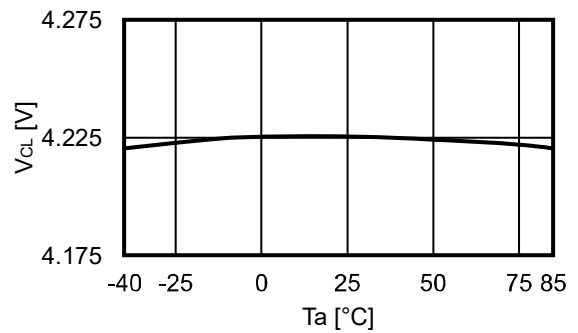


2. Detection voltage, release voltage

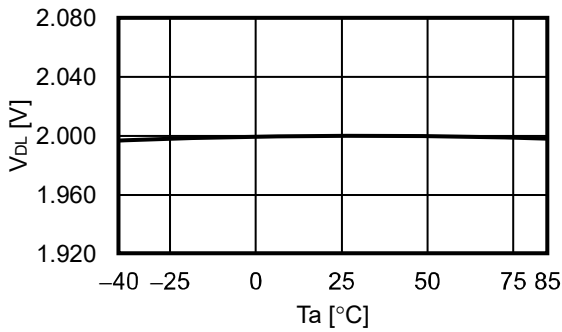
2.1 V_{CU} vs. T_a



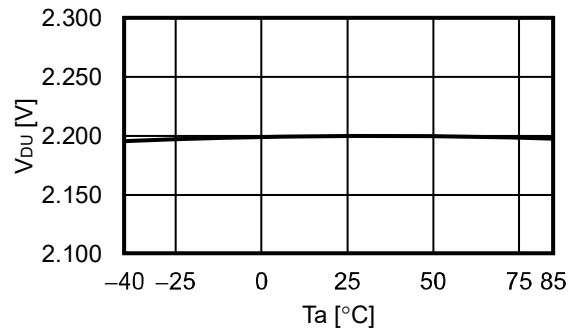
2.2 V_{CL} vs. T_a



2.3 V_{DL} vs. T_a

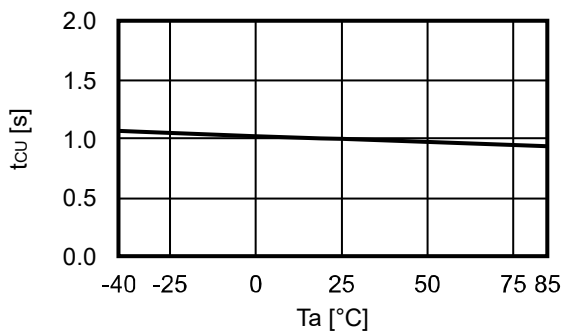


2.4 V_{DU} vs. T_a

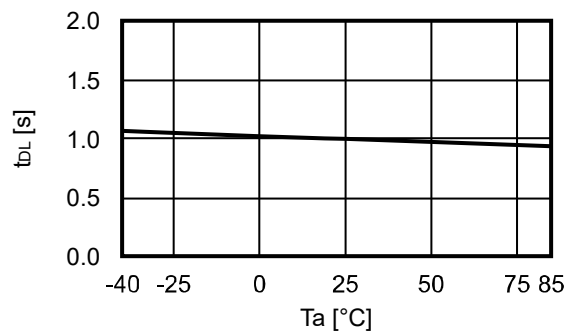


3. Delay time

3.1 t_{CU} vs. T_a

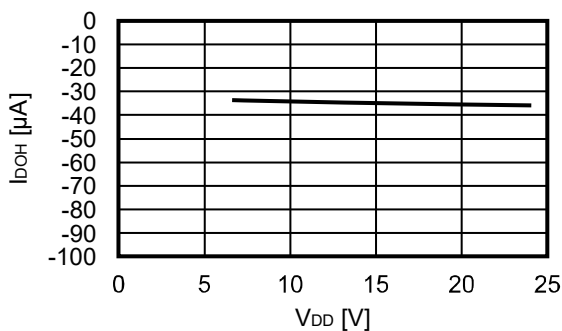


3.2 t_{DL} vs. T_a

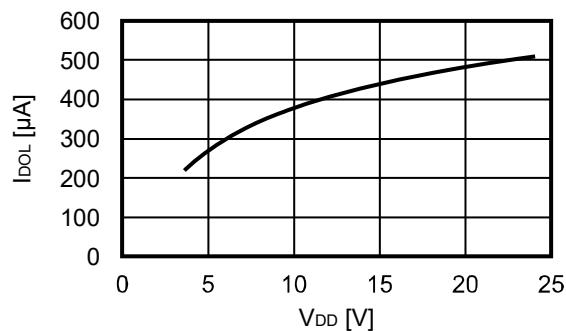


4. Output pin

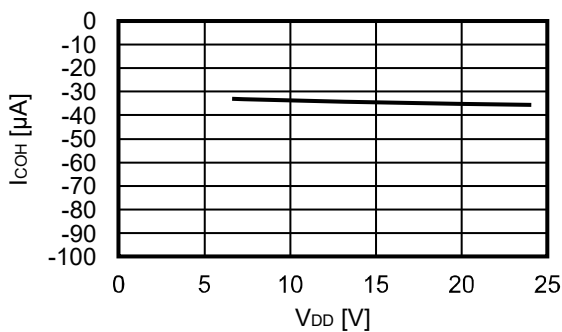
4.1 I_{DOH} vs. V_{DD}



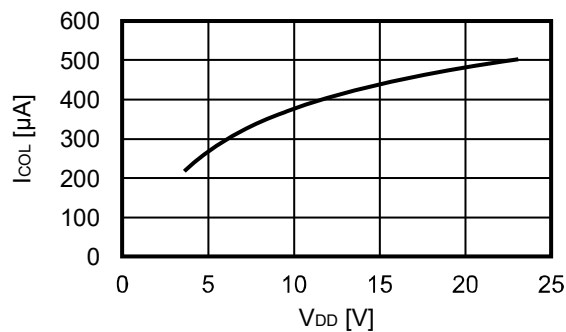
4.2 I_{DOL} vs. V_{DD}



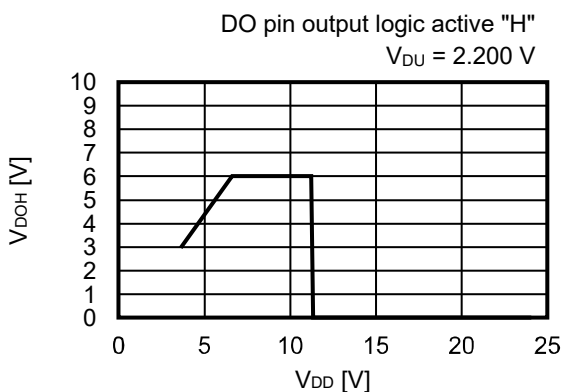
4.3 I_{COH} vs. V_{DD}



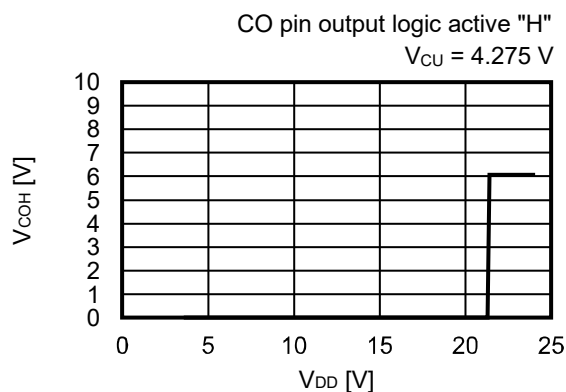
4.4 I_{COL} vs. V_{DD}



4.5 V_{DOH} vs. V_{DD}

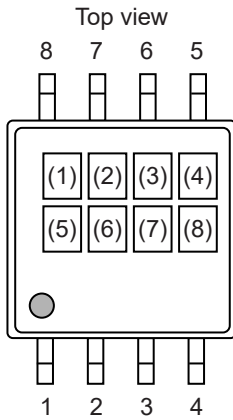


4.6 V_{COH} vs. V_{DD}



■ **Marking Specifications**

1. TMSOP-8

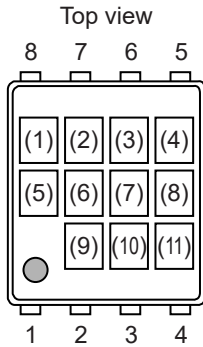


- (1): Blank
- (2) to (4): Product code (refer to **Product name vs. Product code**)
- (5): Blank
- (6) to (8): Lot number

Product name vs. Product code

| Product Name | Product Code | | |
|-----------------|--------------|-----|-----|
| | (2) | (3) | (4) |
| S-82H5BAA-K8T2U | 9 | V | A |

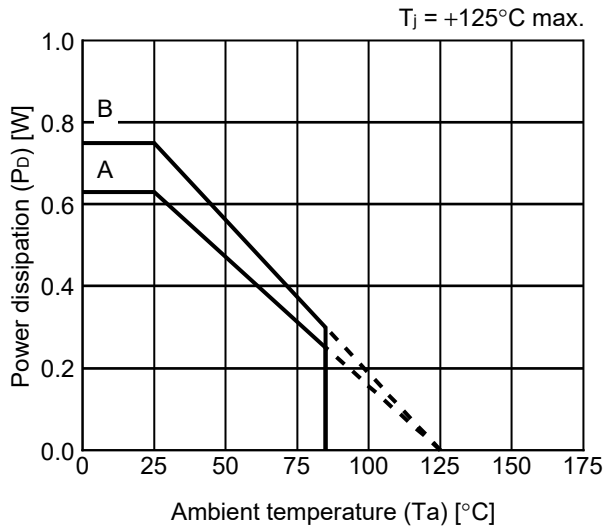
2. SNT-8A



- (1): Blank
- (2) to (4): Product code
- (5), (6): Blank
- (7) to (11): Lot number

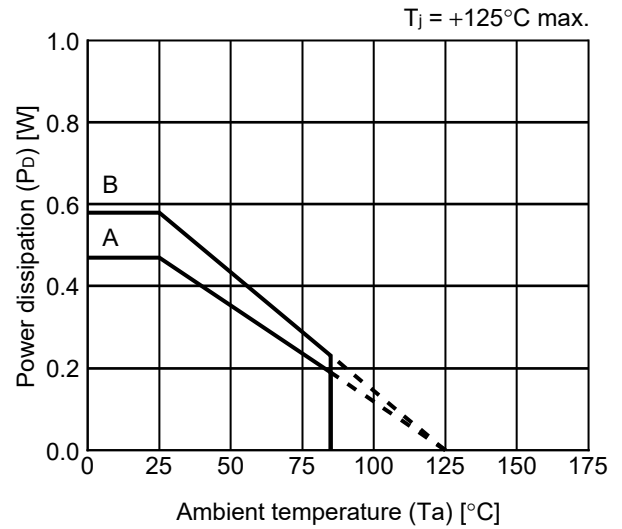
■ **Power Dissipation**

TMSOP-8



| Board | Power Dissipation (P _D) |
|-------|-------------------------------------|
| A | 0.63 W |
| B | 0.75 W |
| C | – |
| D | – |
| E | – |

SNT-8A

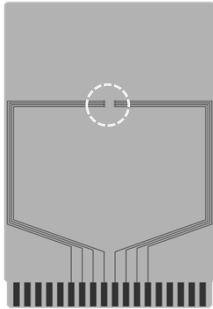


| Board | Power Dissipation (P _D) |
|-------|-------------------------------------|
| A | 0.47 W |
| B | 0.58 W |
| C | – |
| D | – |
| E | – |

TMSOP-8 Test Board

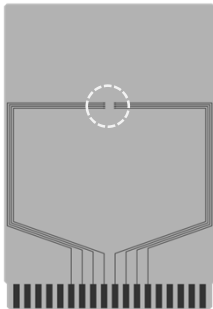
(1) Board A

 IC Mount Area



| Item | Specification | |
|-----------------------------|---------------------|---|
| Size [mm] | 114.3 x 76.2 x t1.6 | |
| Material | FR-4 | |
| Number of copper foil layer | 2 | |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
| | 2 | - |
| | 3 | - |
| | 4 | 74.2 x 74.2 x t0.070 |
| Thermal via | - | |

(2) Board B



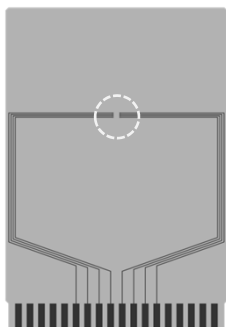
| Item | Specification | |
|-----------------------------|---------------------|---|
| Size [mm] | 114.3 x 76.2 x t1.6 | |
| Material | FR-4 | |
| Number of copper foil layer | 4 | |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
| | 2 | 74.2 x 74.2 x t0.035 |
| | 3 | 74.2 x 74.2 x t0.035 |
| | 4 | 74.2 x 74.2 x t0.070 |
| Thermal via | - | |

No. TMSOP8-A-Board-SD-1.0

SNT-8A Test Board

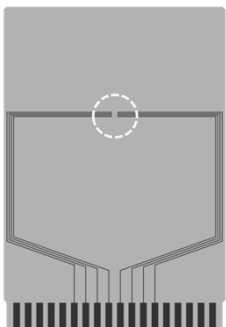
(1) Board A

 IC Mount Area



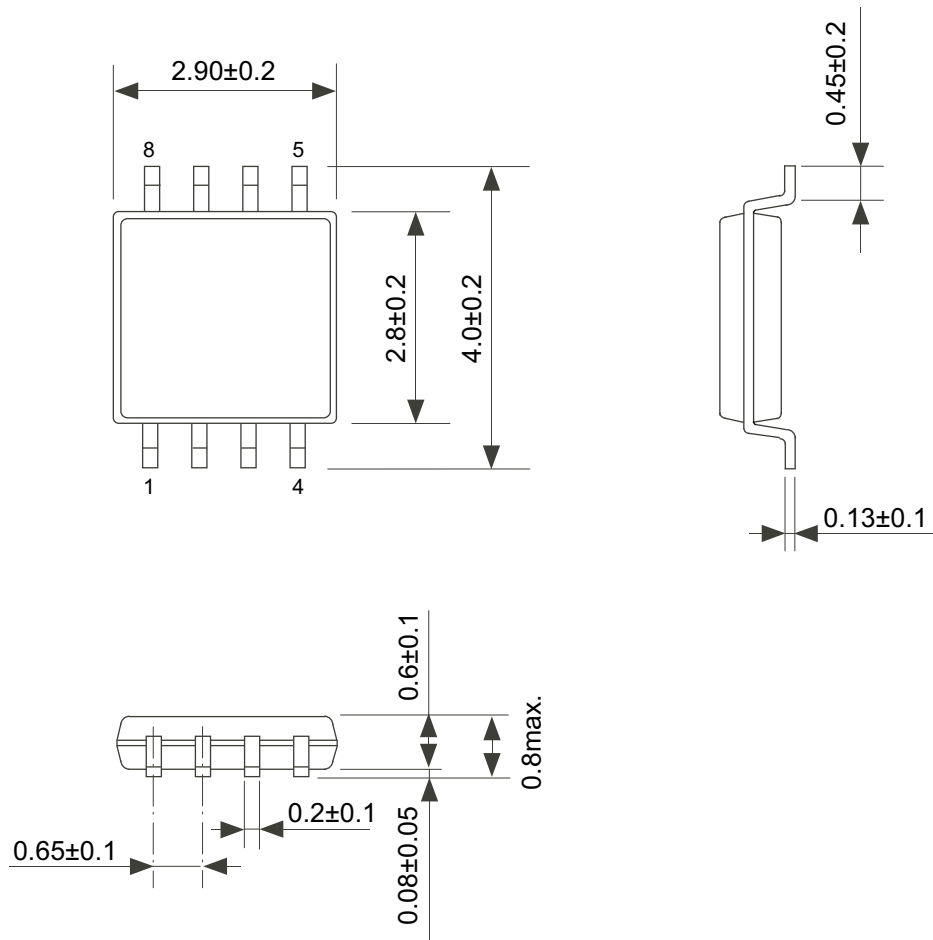
| Item | Specification | |
|-----------------------------|---------------------|---|
| Size [mm] | 114.3 x 76.2 x t1.6 | |
| Material | FR-4 | |
| Number of copper foil layer | 2 | |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
| | 2 | - |
| | 3 | - |
| | 4 | 74.2 x 74.2 x t0.070 |
| Thermal via | - | |

(2) Board B



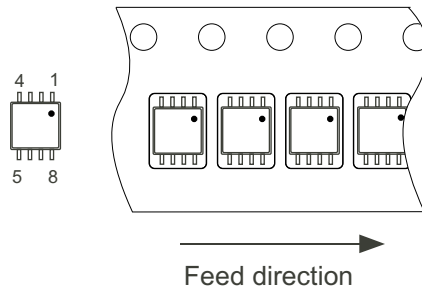
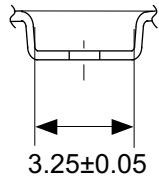
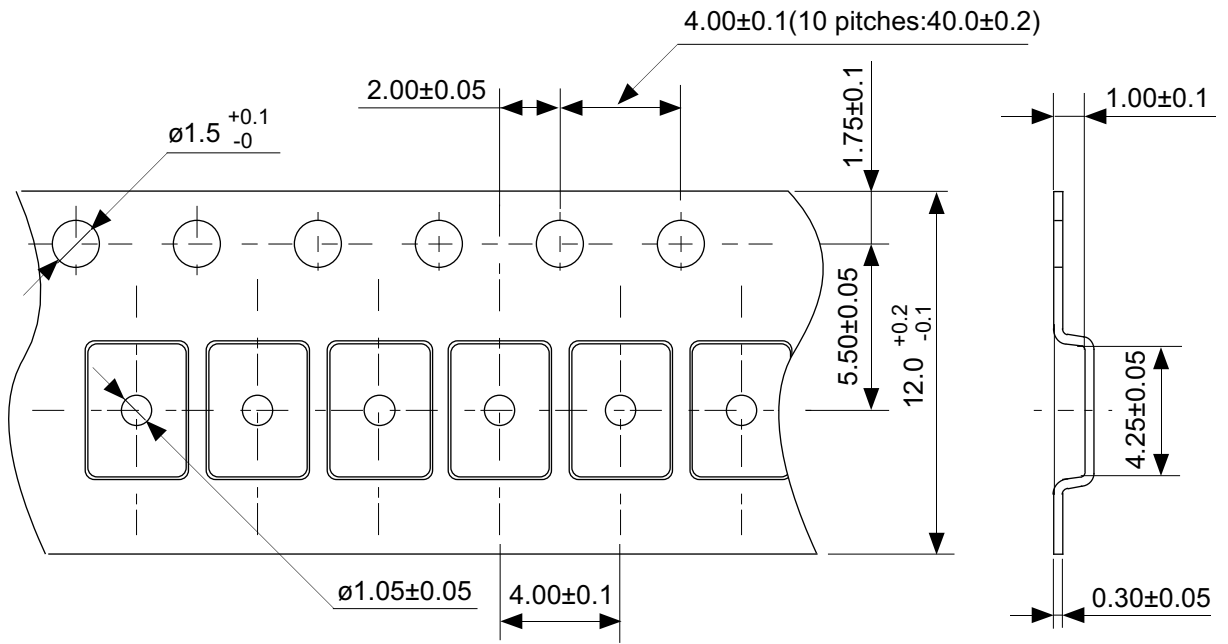
| Item | Specification | |
|-----------------------------|---------------------|---|
| Size [mm] | 114.3 x 76.2 x t1.6 | |
| Material | FR-4 | |
| Number of copper foil layer | 4 | |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
| | 2 | 74.2 x 74.2 x t0.035 |
| | 3 | 74.2 x 74.2 x t0.035 |
| | 4 | 74.2 x 74.2 x t0.070 |
| Thermal via | - | |

No. SNT8A-A-Board-SD-1.0



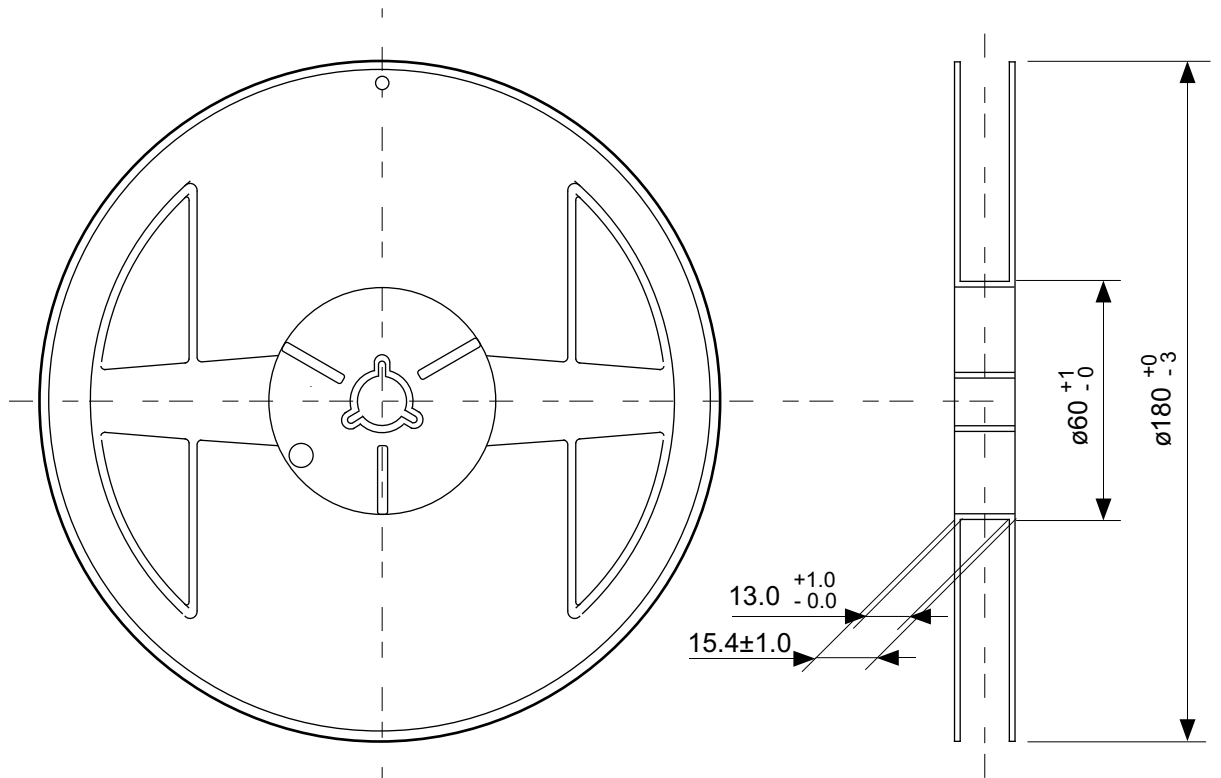
No. FM008-A-P-SD-1.2

| | |
|-------------------|-------------------------|
| TITLE | TMSOP8-A-PKG Dimensions |
| No. | FM008-A-P-SD-1.2 |
| ANGLE | |
| UNIT | mm |
| ABLIC Inc. | |

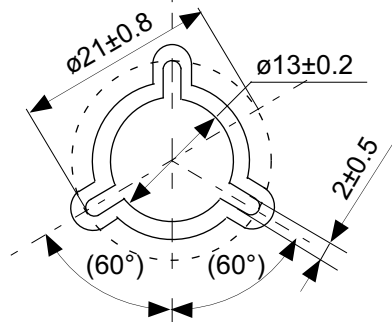


No. FM008-A-C-SD-3.0

| | |
|-------------------|-----------------------|
| TITLE | TMSOP8-A-Carrier Tape |
| No. | FM008-A-C-SD-3.0 |
| ANGLE | |
| UNIT | mm |
| ABLIC Inc. | |

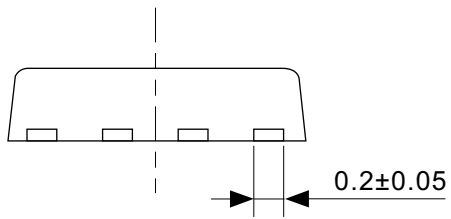
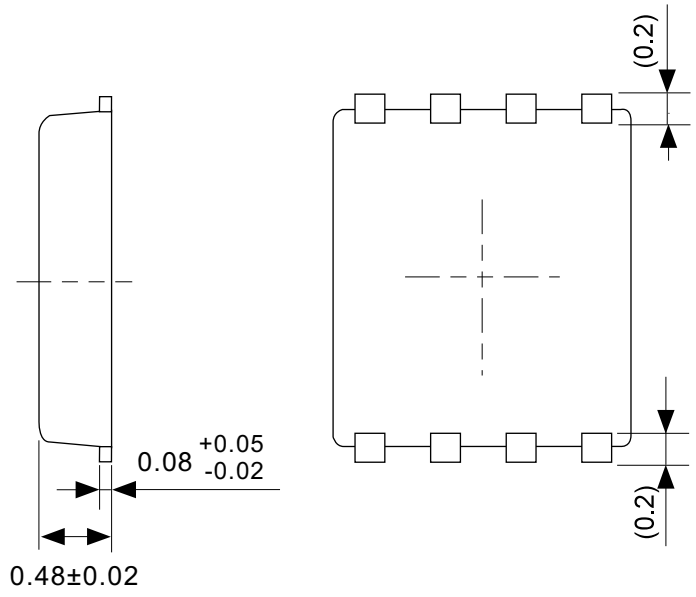
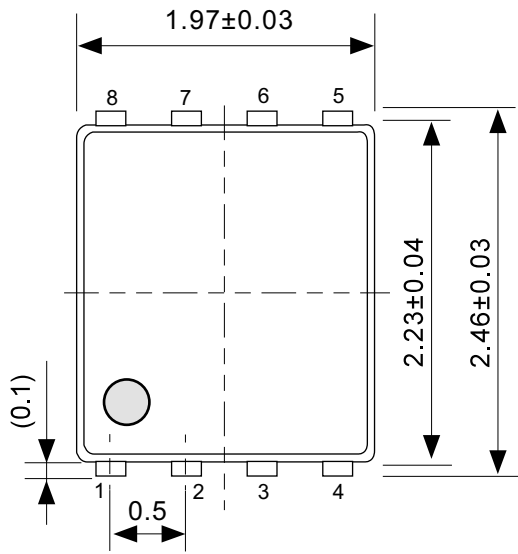


Enlarged drawing in the central part



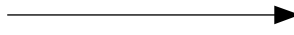
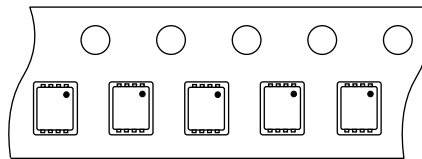
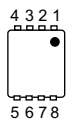
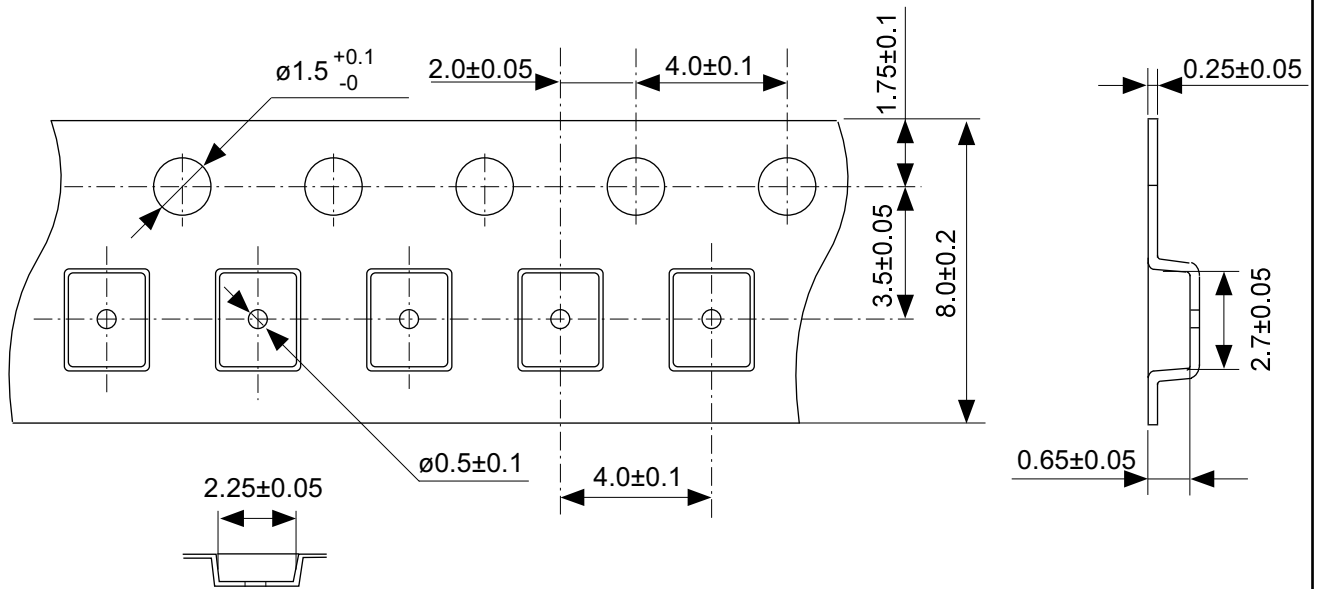
No. FM008-A-R-SD-2.0

| | | | |
|-------------------|------------------|------|-------|
| TITLE | TMSOP8-A-Reel | | |
| No. | FM008-A-R-SD-2.0 | | |
| ANGLE | | QTY. | 4,000 |
| UNIT | mm | | |
| | | | |
| ABLIC Inc. | | | |



No. PH008-A-P-SD-2.1

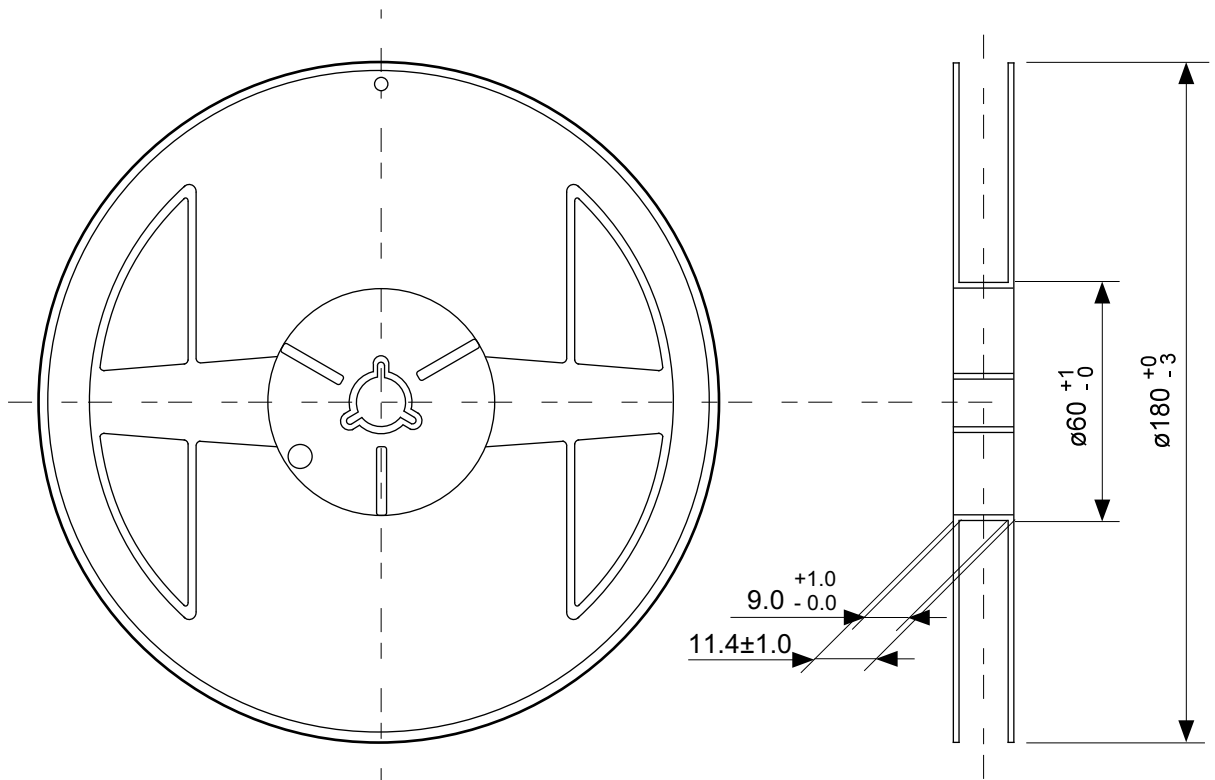
| | |
|-------------------|-------------------------|
| TITLE | SNT-8A-A-PKG Dimensions |
| No. | PH008-A-P-SD-2.1 |
| ANGLE | |
| UNIT | mm |
| ABLIC Inc. | |



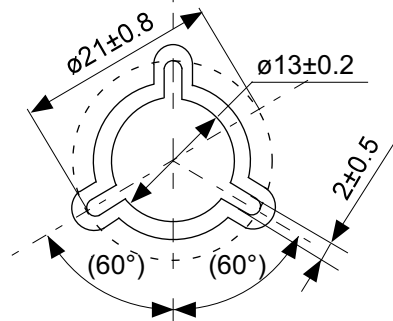
Feed direction

No. PH008-A-C-SD-2.0

| | |
|-------------------|-----------------------|
| TITLE | SNT-8A-A-Carrier Tape |
| No. | PH008-A-C-SD-2.0 |
| ANGLE | |
| UNIT | mm |
| | |
| ABLIC Inc. | |

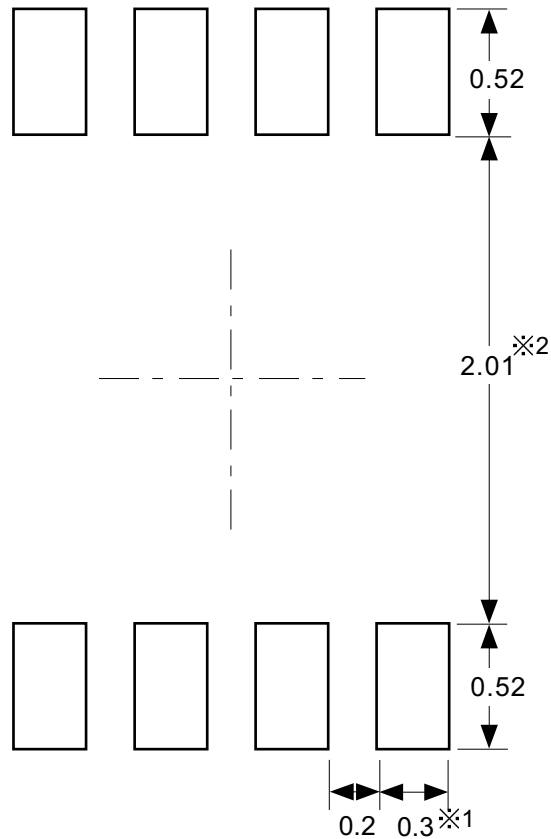


Enlarged drawing in the central part



No. PH008-A-R-SD-2.0

| | | | |
|-------------------|------------------|------|-------|
| TITLE | SNT-8A-A-Reel | | |
| No. | PH008-A-R-SD-2.0 | | |
| ANGLE | | QTY. | 5,000 |
| UNIT | mm | | |
| | | | |
| ABLIC Inc. | | | |



※1. ランドパターンの幅に注意してください (0.25 mm min. / 0.30 mm typ.).
 ※2. パッケージ中央にランドパターンを広げないでください (1.96 mm ~ 2.06 mm)。

- 注意
1. パッケージのモールド樹脂下にシルク印刷やハンダ印刷などしないでください。
 2. パッケージ下の配線上のソルダーレジストなどの厚みをランドパターン表面から0.03 mm以下にしてください。
 3. マスク開口サイズと開口位置はランドパターンと合わせてください。
 4. 詳細は“SNTパッケージ活用の手引き”を参照してください。

※1. Pay attention to the land pattern width (0.25 mm min. / 0.30 mm typ.).
 ※2. Do not widen the land pattern to the center of the package (1.96 mm to 2.06mm).

- Caution**
1. Do not do silkscreen printing and solder printing under the mold resin of the package.
 2. The thickness of the solder resist on the wire pattern under the package should be 0.03 mm or less from the land pattern surface.
 3. Match the mask aperture size and aperture position with the land pattern.
 4. Refer to "SNT Package User's Guide" for details.

※1. 请注意焊盘模式的宽度 (0.25 mm min. / 0.30 mm typ.).
 ※2. 请勿向封装中间扩展焊盘模式 (1.96 mm ~ 2.06 mm)。

- 注意
1. 请勿在树脂型封装的下面印刷丝网、焊锡。
 2. 在封装下、布线上的阻焊膜厚度 (从焊盘模式表面起) 请控制在 0.03 mm 以下。
 3. 钢网的开口尺寸和开口位置请与焊盘模式对齐。
 4. 详细内容请参阅 "SNT 封装的应用指南"。

No. PH008-A-L-SD-4.1

| | |
|-------------------|----------------------------------|
| TITLE | SNT-8A-A -Land Recommendation |
| No. | PH008-A-L-SD-4.1 |
| ANGLE | |
| UNIT | mm |
| | |
| ABLIC Inc. | |

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The entire system in which the products are used must be sufficiently evaluated and judged whether the products are allowed to apply for the system on customer's own responsibility.
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2.4-2019.07